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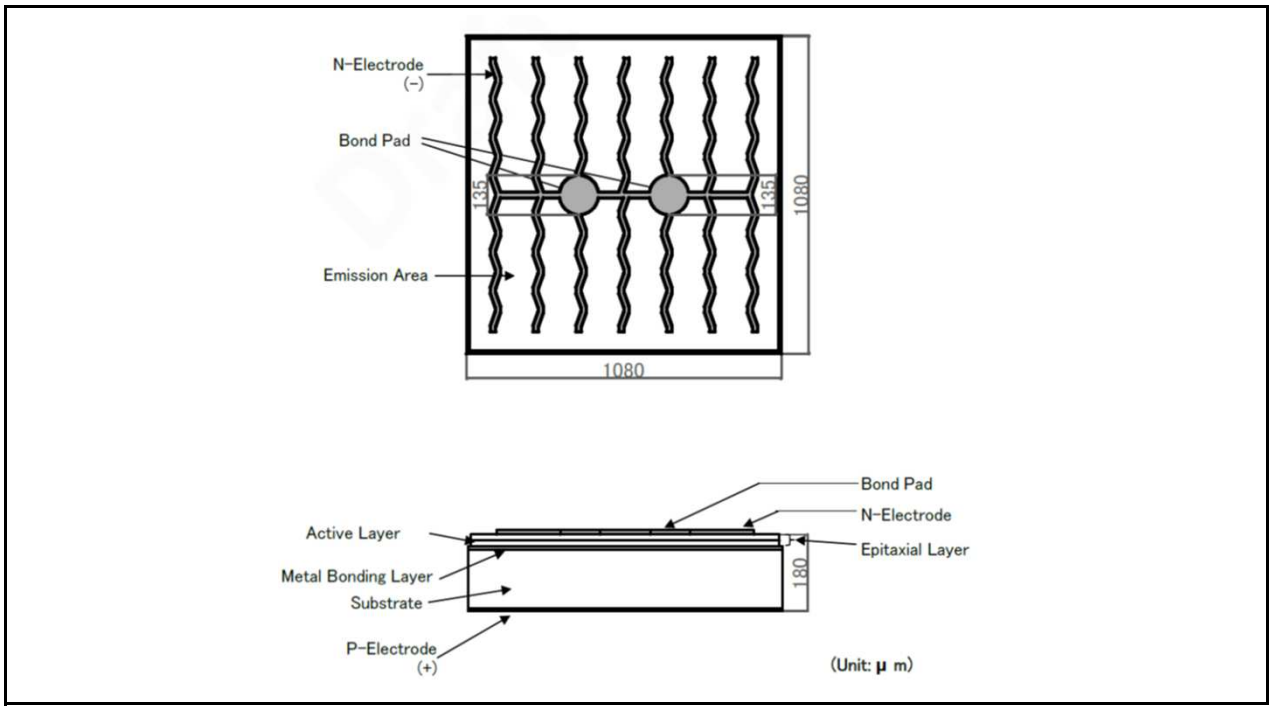
Data Sheet **Preliminary**

Infrared LED Chip **EOLC-1450-21**

Rev. 01, 2019

Radiation	Type	Electrodes
Infrared	InGaAs - based material	n (cathode) up



Die size (typ.): 1.080 mm × 1.080 mm (42 mil)
Thickness (typ.): 0.180 mm (7 mil)
Bond pads size: Ø 0.130 mm (perifery = Ø 0.135 mm)
Contact metallization anode and cathode: gold alloy

Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Continuous forward current*		I_F	1000	mA
Reverse current		I_R	10	µA

*For reference only

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Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		1		V
Radiant power*	I_F=20 mA	Φ_e		3		mW
Peak wavelength	I_F=20 mA	λ_p	1400	1450	1500	nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		75		nm
Forward voltage	I_F=350 mA	V_F		1	1.4	V
Radiant power*	I_F=350 mA	Φ_e		30		mW
Peak wavelength	I_F=350 mA	λ_p	1400	1450	1500	nm
FWHM	I_F=350 mA	$\Delta\lambda_{0.5}$		75		nm
Forward voltage	I_F=1000 mA	V_F		1	1.5	V
Radiant power*	I_F=1000 mA	Φ_e		50		mW
Peak wavelength	I_F=1000 mA	λ_p	1400	1450	1500	nm
FWHM	I_F=1000 mA	$\Delta\lambda_{0.5}$		75		nm

*Measured on silicon covered chip on star board

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